

Code: 20EE3301, 20EC3301

**II B.Tech - I Semester – Regular/Supplementary Examinations
DECEMBER 2022**

**ELECTRONIC DEVICES AND AMPLIFIER CIRCUITS
(Common for EEE, ECE)**

Duration: 3 hours

Max. Marks: 70

Note: 1. This paper contains questions from 5 units of Syllabus. Each unit carries 14 marks and have an internal choice of Questions.

2. All parts of Question must be answered in one place.

BL – Blooms Level

CO – Course Outcome

			BL	CO	Max. Marks
UNIT-I					
1	a)	Define transistor and explain different modes of BJT.	L2	CO1	7 M
	b)	What is the need of biasing in BJT amplifier circuits? And explain any one type of biasing in BJT amplifier.	L2	CO1	7 M
OR					
2	a)	How BJT works as a switch & an amplifier and analyze with examples.	L4	CO2	7 M
	b)	A BJT having $\beta=100$ is biased at a dc collector current of 1mA. Find the value of g_m , r_e and r_π at the bias point.	L3	CO4	7 M
UNIT-II					
3	a)	Explain the small signal operation of the enhancement MOSFET amplifier and derive voltage gain.	L3	CO2	7 M

	b)	Derive the expression for the voltage gain of Common source amplifier and Common drain amplifier configuration, under small signal low frequency conditions.	L3	CO2	7 M
OR					
4	a)	Outline the Biasing in MOS Amplifier Circuits.	L2	CO4	7 M
	b)	Draw and explain I-V characteristic of MOSFET.	L2	CO1	7 M
UNIT-III					
5	a)	Solve the mid band gain AM and the upper 3-dB frequency f_H of a CS amplifier fed with a signal source having an internal resistance $R_{sig}=100k\Omega$. The amplifier has $R_G=4.7M \Omega$, $R_D=R_L=15k \Omega$, $g_m=1mA/V$, $r_0=150k \Omega$, $C_{gs}=1pF$ and $C_{gd}=0.4pF$.	L3	CO3	7 M
	b)	For the amplifier in Figure below determine the input impedance and load voltage. $V_{in}= 10 \text{ mV}$, $V_{DD} = 12$, $R_G = 1M\Omega$, $R_D = 1.5 \text{ k}\Omega$, $R_{SW} = 10 \Omega$, $R_S = 200 \Omega$, $R_L=12 \text{ k}\Omega$, $I_{DSS}=20 \text{ mA}$, $V_{GS(off)}= -1V$.	L3	CO3	7 M

OR					
6	a)	Explain MOSFET internal capacitances and high frequency model in brief.	L2	CO3	7 M
	b)	Explain in brief the Low and High Frequency Response of Common source model.	L2	CO1	7 M
UNIT-IV					
7	a)	Derive gain, input and output impedance of Differential gain of the active loaded MOS pair.	L3	CO3	7 M
	b)	A MOS differential pair is driven with an input CM level of 1.6V. If $I_{SS}=1mA$, $V_{TH}=0.5 V$, $K_n^1 \left(\frac{W}{L}\right) = 4mA/V^2$, $V_{D1}=1V$ and $V_{DD}=2 V$, what is the maximum allowable load resistance?	L3	CO3	7 M
OR					
8	a)	Explain two stages CMOS OP-AMP with neat diagram.	L2	CO3	7 M
	b)	A MOS differential amplifier is operated at a total current of 0.8mA, using transistors with a W/L ratio of 100, $kn'=\mu_n C_{ox}=0.2mA/V^2$, $V_A=20V$, and $R_D=5k\Omega$. Find $V_{ov}=(V_{GS}-V_t)$, g_m , r_o , and A_d .	L4	CO3	7 M
UNIT-V					
9	a)	Analyze and explain basic MOSFET current source with neat diagram.	L4	CO4	7 M
	b)	Construct the basic MOSFET current steering circuits with working principle.	L3	CO4	7 M

OR

10	a)	Compare important characteristics of MOSFET and BJT.	L4	CO4	7 M
	b)	What is MOSFET and classify the MOSFET and write the advantages and Applications of MOSFET over BJT.	L2	CO4	7 M